TOSHIBA Diode Silicon Epitaxial Planar Type

# HN2D01FU

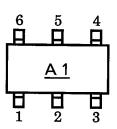
#### Ultra High Speed Switching Application

HN2D01FU is composed of 3 independent diodes.  $V_{F}(3) = 0.98V \text{ (typ.)}$ Low forward voltage Fast reverse recovery time:  $t_{rr} = 1.6$ ns (typ.)  $: C_T = 0.5pF (typ.)$ 

#### Pin Assignment (Top View)

Small total capacitance

#### Marking



#### Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit	
Maximum (peak) reverse Voltage	$V_{RM}$	85	V	
Reverse voltage	$V_{R}$	80	V	
Maximum (peak) forward current	I <sub>FM</sub>	240 *	mA	
Average forward current	Io	80 *	mA	
Surge current (10ms)	I <sub>FSM</sub>	1 *	Α	
Power dissipation	Р	200	mW	
Junction temperature	Tj	125	°C	
Storage temperature	T <sub>stg</sub>	<b>−</b> 55~125	°C	

## Unit in mm $2.1 \pm 0.1$ **CATHODE** 2. **CATHODE CATHODE** 4 ANODE 5. ANODE ANODE JEDEC **EIAJ TOSHIBA** 1-2T1C

Weight: 6.2mg

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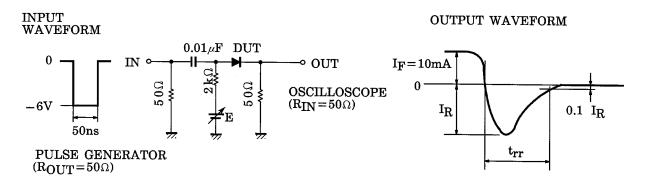
<sup>:</sup> This is maximum rating of single diode (Q1 or Q2 or Q3). In the case of using 2 ro 3 diodes, the maximum ratings per diodes is 75 % of the single diode one.



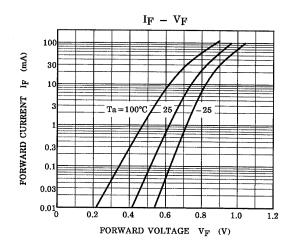
### Electrical Characteristics (Q1 Q2 Q3 Common, Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Forward voltage	V <sub>F (1)</sub>	_	I <sub>F</sub> = 1mA		0.62	_	V
	V <sub>F (2)</sub>	_	I <sub>F</sub> = 10mA	I	0.75	_	
	V <sub>F (3)</sub>	_	I <sub>F</sub> = 100mA		0.98	1.20	
Reverse current	I <sub>R (1)</sub>	_	V <sub>R</sub> = 30V	I	_	0.1	μΑ
	I <sub>R (2)</sub>	_	V <sub>R</sub> = 80V	ı	_	0.5	
Total capacitance	Ст	_	$V_R = 0$ , $f = 1MH_Z$		0.5	3.0	pF
Reverse recovery time	t <sub>rr</sub>	_	I <sub>F</sub> = 10mA (Fig.1)		1.6	4.0	ns

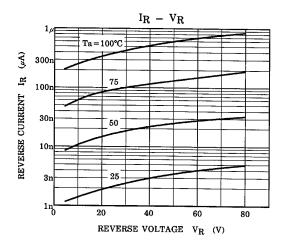
Fig.1 Reverse Recovery Time (trr) Test Circuit



Q1, Q2, Q3 Common



Q1, Q2, Q3 Common



Q1, Q2, Q3 Common

